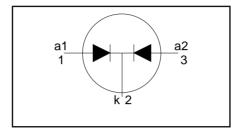
# PBYR1045CTD series

### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

### **SYMBOL**



### QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{O(AV)} = 10 \text{ A}$ 
 $V_F \le 0.6 \text{ V}$ 

#### **GENERAL DESCRIPTION**

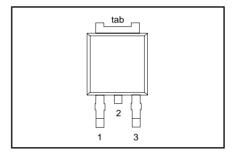
Dual schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR1045CTD series is supplied in the SOT428 surface mounting package.

### **PINNING**

PIN	DESCRIPTION
1	anode 1
2	cathode <sup>1</sup>
3	anode 2
tab	cathode

#### **SOT428**



# **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
		PBYR10		40CTD	45CTD	
$V_{RRM}$	Peak repetitive reverse voltage		-	40	45	V
$V_{RWM}$	Working peak reverse voltage		-	40	45	V
$V_R$	Continuous reverse voltage	T <sub>mb</sub> ≤ 108 °C	-	40	45	V
I <sub>O(AV)</sub>	Average rectified forward current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{mb} \le 127 ^{\circ}C$	-	10	)	A
I <sub>FRM</sub>	Repetitive peak forward current per diode	square wave; $\delta = 0.5$ ; $T_{mb} \le 127 ^{\circ}\text{C}$	-	10	)	A
I <sub>FSM</sub>	Non-repetitive peak forward	t = 10 ms	-	10		Α
	current per diode	t = 8.3  ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM}(\text{max})}$	-	11	0	A
I <sub>RRM</sub>	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T <sub>i max</sub>	-	1		A
T <sub>j</sub>	Operating junction temperature	Jiliax	-	15	0	°C
T <sub>stg</sub>	Storage temperature		- 65	17	5	°C

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<sup>1</sup> it is not possible to make connection to pin 2 of the SOT428 package

# PBYR1045CTD series

# THERMAL RESISTANCES

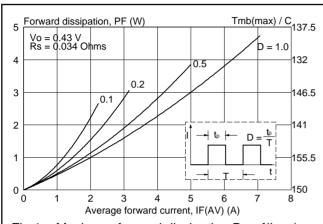
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th i-a</sub>	to mounting base	per diode both diodes pcb mounted, minimum footprint, FR4 board		- - 50	4.5 3 -	K/W K/W K/W

# **ELECTRICAL CHARACTERISTICS**

All characteristics are per diode at  $T_i = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{F}$	Forward voltage	$I_{\rm F} = 5 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.52	0.6	V
	_	$I_{\rm F} = 10  {\rm A};  T_{\rm i} = 125  {\rm C}$	-	0.7	0.77	V
		$I_{\rm F} = 10  {\rm A}^{\circ}$	-	0.72	0.87	V
I <sub>R</sub>	Reverse current	$\dot{V}_R = V_{RWM}$	-	0.06	0.5	mΑ
		$V_{R} = V_{RWM}$ ; $T_{i} = 100^{\circ}C$	-	6	15	mΑ
$C_d$	Junction capacitance	$V_R = 5 \text{ V}; \text{ f} = 1 \text{ MHz}, T_j = 25 ^{\circ}\text{C} \text{ to } 125 ^{\circ}\text{C}$	-	155	-	pF

## PBYR1045CTD series



Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$ .

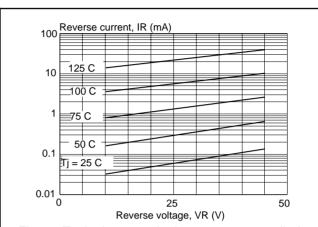


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_i$ 

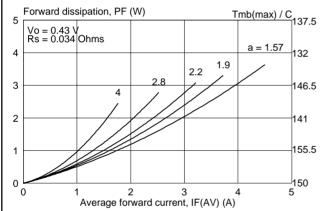


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = form $factor = I_{F(RMS)} / I_{F(AV)}$ .

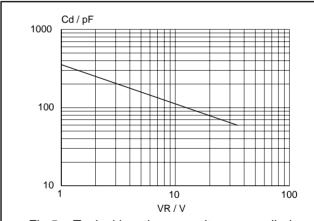
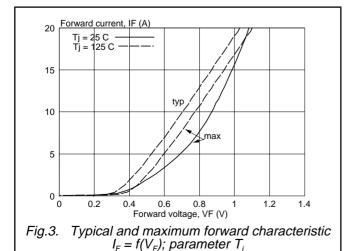
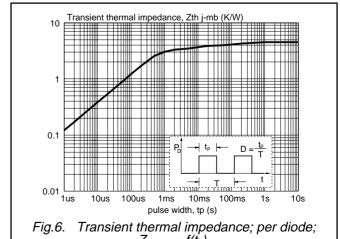


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125°C.

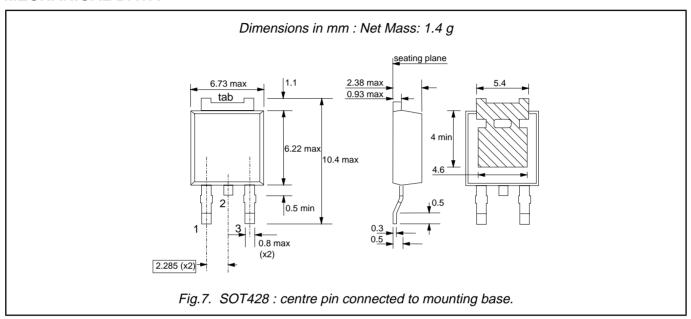




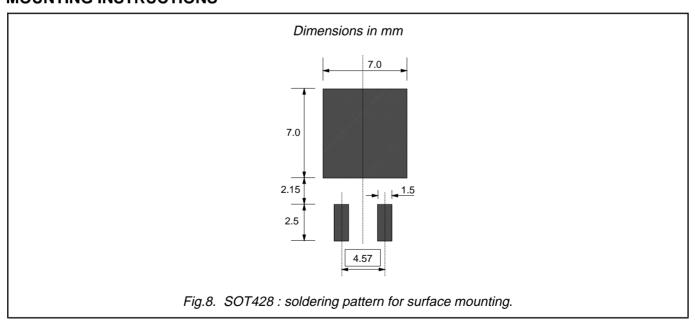
 $Z_{th\ j-mb} = f(t_p).$ 

PBYR1045CTD series

### **MECHANICAL DATA**



# **MOUNTING INSTRUCTIONS**



#### **Notes**

- Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

# Rectifier diodes Schottky barrier

PBYR1045CTD series

#### **DEFINITIONS**

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published late				
Product specification	This data sheet contains final product specifications.			
Limiting values				

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of

this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

## **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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